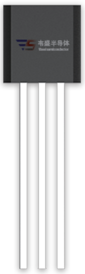
M8550 TRANSISTOR (PNP)

FEATURES

- Power Dissipation



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
M8550	TO-92	Bulk	1000pcs/Bag
M8550-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-800	mA
P_C	Collector Power Dissipation	625	mW
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= -100μA, I_E=0	-40		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$*	I_C= -0.1mA , I_B=0	-25		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100μA, I_C=0	-6		V
Collector cut-off current	I_{CBO}	V_{CB}= -35V , I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -20V , I_B=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-5mA	45		
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-100mA	80	400	
	$h_{FE(3)}$	V_{CE}=-1V, I_C=-800mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -800mA, I_B=-80mA		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-800mA, I_B=-80mA		-1.2	V
Transition frequency	f_T	V_{CE}=-6V, I_C= -20mA f=30MHz	150		MHz

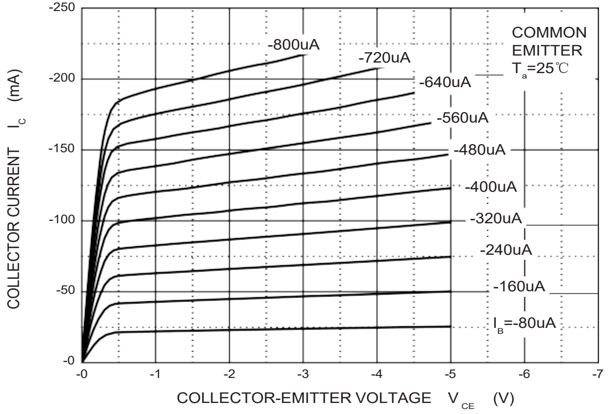
*Pulse Test: pulse width ≤ 300μs,duty cycle ≤2%.

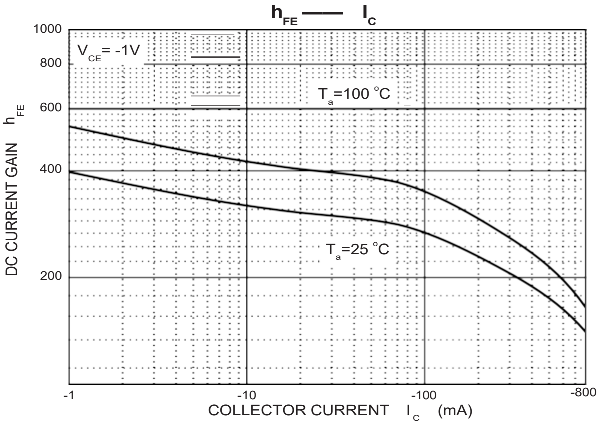
CLASSIFICATION OF $h_{FE(2)}$

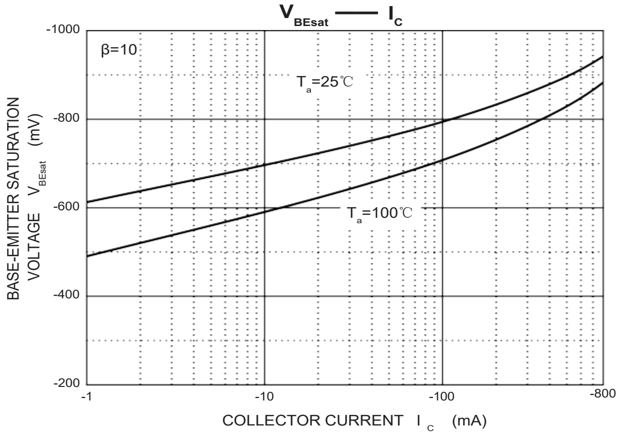
Rank	**B**	**C**	**D**	**D3**
Range	80-160	120-200	160-300	300-400

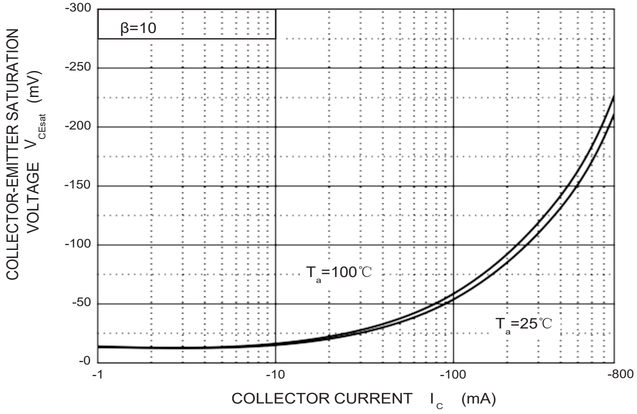
Typical Characteristics

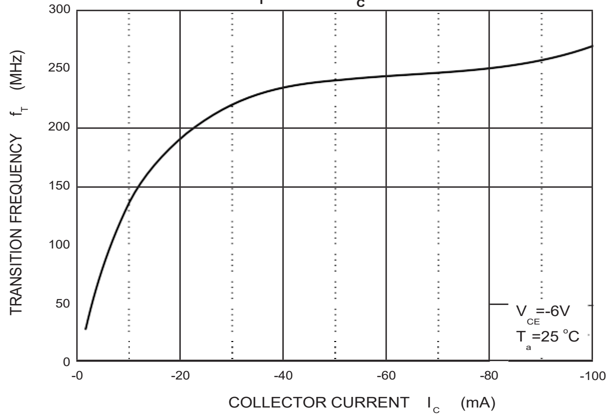
M8550

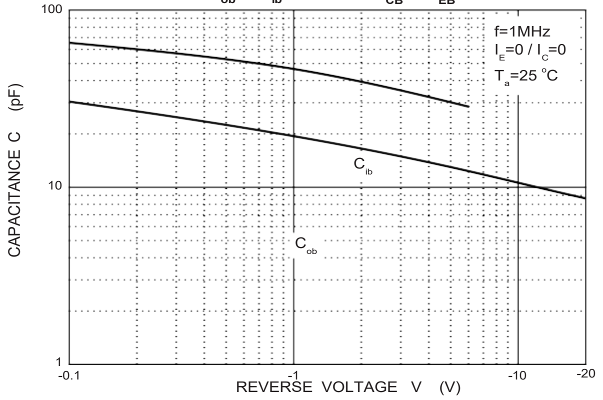

Static Characteristic

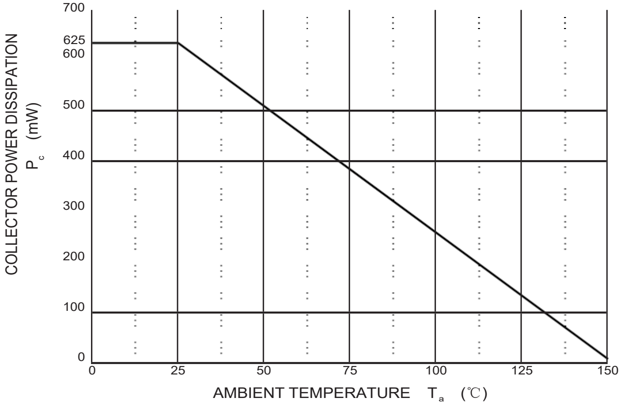

h_{FE} —— I_C


V_{BEsat} —— I_C


V_{CEsat} —— I_C


f_T —— I_C


C_{ob} / C_{ib} —— V_{CB} / V_{EB}


P_c —— T_a